

# Vishay Semiconductors

# Silicon PIN Photodiode



VBP104FAS and VBP104FASR are high speed and high sensitive PIN photodiodes. It is a surface mount device (SMD) including the chip with a 4.4 mm<sup>2</sup> sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength 870 nm or 950 nm.

#### **FEATURES**

Package type: surface mount





• Radiant sensitive area (in mm2): 4.4

High radiant sensitivity

 Daylight blocking filter matched with 870 nm to 950 nm emitters

· Fast response times

• Angle of half sensitivity:  $\varphi = \pm 65^{\circ}$ 

• Floor life: 168 h, MSL 3, acc. J-STD-020

• Lead (Pb)-free reflow soldering

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### **APPLICATIONS**

- · High speed detector for infrared radiation
- Infrared remote control and free air data transmissionsystems, e.g. in combination with TSFFxxxx series IR emitters

PRODUCT SUMMARY					
COMPONENT	I <sub>ra</sub> (μΑ)	φ <b>(deg)</b>	$\lambda_{0.5}$ (nm)		
VBP104FAS	35	± 65	780 to 1050		
VBP104FASR	35	± 65	780 to 1050		

#### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
VBP104FAS	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing		
VBP104FASR	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing		

#### Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	60	V	
Power dissipation	T <sub>amb</sub> ≤ 25 °C	P <sub>V</sub>	215	mW	
Junction temperature		T <sub>j</sub>	100	°C	
Operating temperature range		T <sub>amb</sub>	- 40 to + 100	°C	
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C	
Soldering temperature	Acc. reflow sloder profile fig. 8	T <sub>sd</sub>	260	°C	
Thermal resistance junction/ambient		R <sub>thJA</sub>	350	K/W	

#### Note

T<sub>amb</sub> = 25 °C, unless otherwise specified

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BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 50 mA	V <sub>F</sub>		1	1.3	V
Breakdown voltage	I <sub>R</sub> = 100 μA, E = 0	V <sub>(BR)</sub>	60			V
Reverse dark current	V <sub>R</sub> = 10 V, E = 0	I <sub>ro</sub>		2	30	nA
Diada assasitansa	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	C <sub>D</sub>		48		pF
Diode capacitance	V <sub>R</sub> = 3 V, f = 1 MHz, E = 0	C <sub>D</sub>		17	40	pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of V <sub>o</sub>	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK <sub>Vo</sub>		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	l <sub>k</sub>		32		μΑ
Temperature coefficient of I <sub>k</sub>	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK <sub>lk</sub>		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \ \lambda = 950 \text{ nm}, \\ V_R = 5 \text{ V}$	I <sub>ra</sub>	25	35		μΑ
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λρ		950		nm
Range of spectral bandwidth		λ 0.5		780 to 1050		nm
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4 x 10 <sup>-14</sup>		W/√Hz
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t <sub>r</sub>		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t <sub>f</sub>		100		ns

#### Note

T<sub>amb</sub> = 25 °C, unless otherwise specified

### **BASIC CHARACTERISTICS**

 $T_{amb}$  = 25 °C, unless otherwise specified

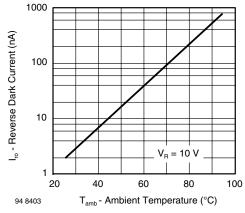


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

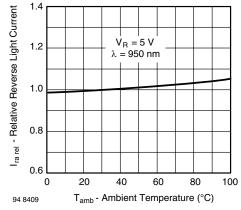


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



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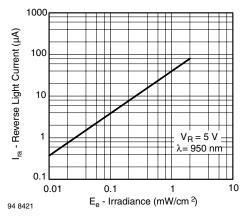


Fig. 3 - Reverse Light Current vs. Irradiance

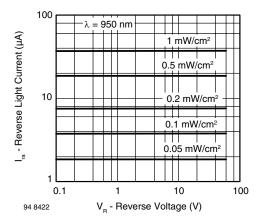


Fig. 4 - Reverse Light Current vs. Reverse Voltage

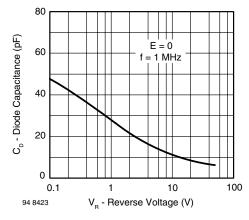


Fig. 5 - Diode Capacitance vs. Reverse Voltage

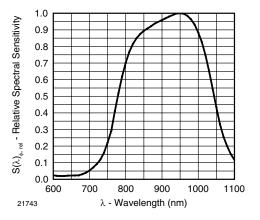


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

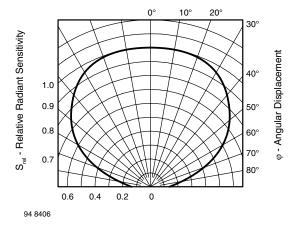


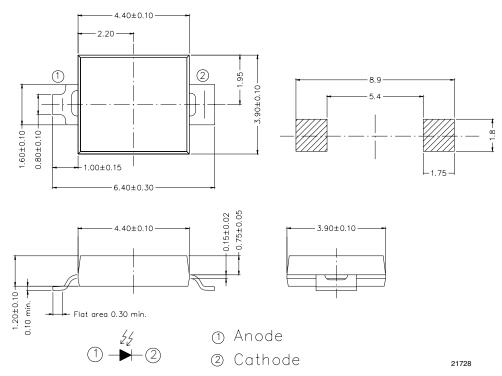
Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

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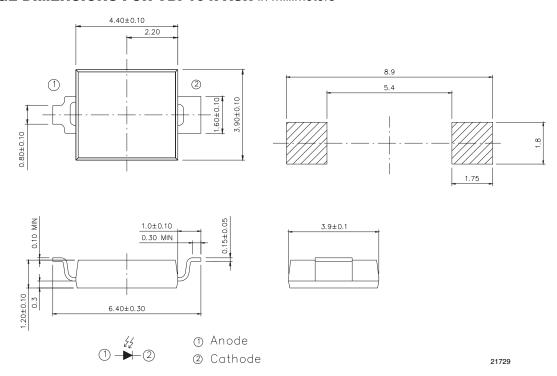
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### **PACKAGE DIMENSIONS FOR VBP104FAS** in millimeters



#### **PACKAGE DIMENSIONS FOR VBP104FASR** in millimeters

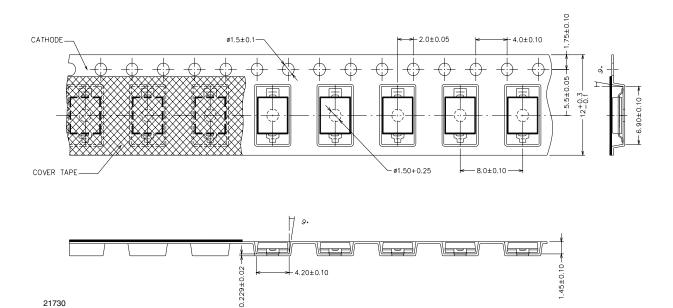


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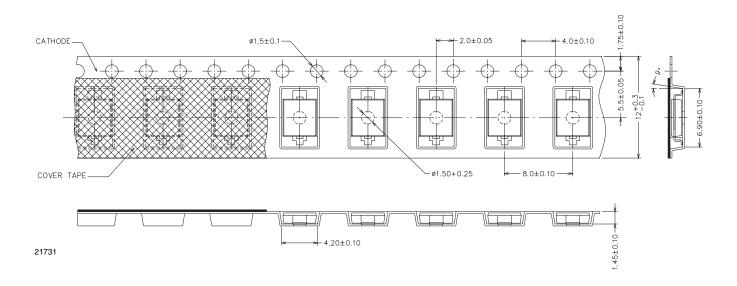
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### **TAPING DIMENSIONS FOR VBP104FAS** in millimeters

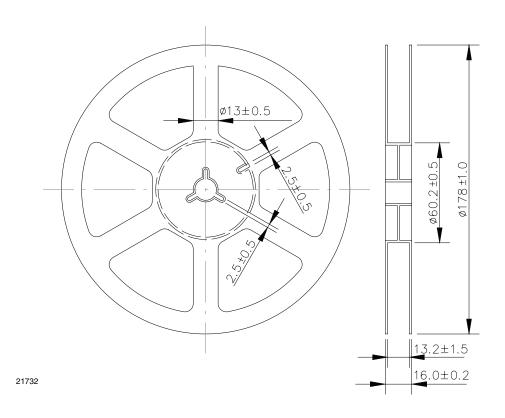


### TAPING DIMENSIONS FOR VBP104FASR in millimeters





#### REEL DIMENSIONS FOR VBP104FAS AND VBP104FASR in millimeters



#### **SOLDER PROFILE**

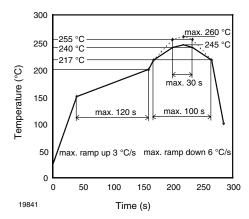


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

#### **DRYPACK**

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

### **FLOOR LIFE**

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

Floor life: 168 h

Conditions:  $T_{amb}$  < 30 °C, RH < 60 %

#### **DRYING**

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions:

192 h at 40 °C (+ 5 °C), RH < 5 %

or

96 h at 60 °C (+ 5 °C), RH < 5 %.



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